

FDZ4670

N-Channel PowerTrench® MOSFET BGA

30V, 25A, 2.5mΩ

Features

- Max $r_{DS(on)}$ = 2.5mΩ at $V_{GS} = 10V$, $I_D = 25A$
- Max $r_{DS(on)}$ = 4.5mΩ at $V_{GS} = 4.5V$, $I_D = 18.5A$
- Ultra-thin package: less than 0.85mm height when mounted to PCB
- Outstanding thermal transfer characteristics
- Ultra-low gate charge x $r_{DS(on)}$ product
- RoHS Compliant



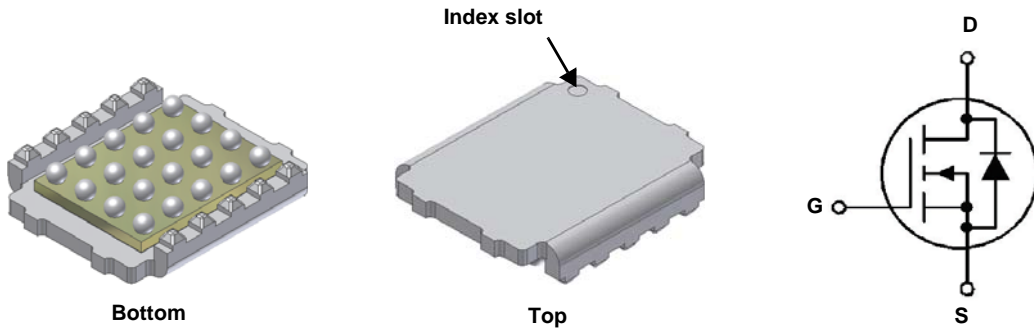
General Description

Combining Fairchild's 30V PowerTrench process with state-of-the-art BGA packaging, the FDZ4670 minimize both PCB space and $r_{DS(on)}$. This BGA MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, high current handling capacity, ultra-low profile packaging, low gate charge and low $r_{DS(on)}$.

This MOSFET feature faster switching and lower gate charge than other MOSFETs with comparable $r_{DS(on)}$ specifications resulting in DC/DC power supply designs and POL converters with higher overall efficiency.

Applications

- DC - DC Conversion
- POL converters



FLFBGA 3.5X4.0

MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current -Continuous (Note 1a)	25	A
	-Pulsed	60	
P_D	Power Dissipation (Note 1a)	2.5	W
	Power Dissipation (Note 1b)	1.25	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	100	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.85	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
4670	FDZ4670	FLFBGA 3.5X4.0	13"	12mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		-30		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	1	1.7	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		4.4		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 25\text{A}$		1.9	2.5	m Ω
		$V_{GS} = 4.5\text{V}, I_D = 18.5\text{A}$		3.0	4.5	
		$V_{GS} = 10\text{V}, I_D = 25\text{A}, T_J = 125^\circ\text{C}$		2.6	3.8	
g_{FS}	Forward Transconductance	$V_{DD} = 10\text{V}, I_D = 25\text{A}$		114		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$		2660	3540	pF
C_{oss}	Output Capacitance			1440	1920	pF
C_{rss}	Reverse Transfer Capacitance			180	270	pF
R_g	Gate Resistance	$f = 1\text{MHz}$		1.0		Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{V}, I_D = 1.0\text{A},$ $V_{GS} = 10\text{V}, R_{GEN} = 6\Omega$		15	27	ns
t_r	Rise Time			11	20	ns
$t_{d(off)}$	Turn-Off Delay Time			50	80	ns
t_f	Fall Time			67	107	ns
Q_g	Total Gate Charge	$V_{GS} = 10\text{V}, V_{DD} = 15\text{V},$ $I_D = 25\text{A}$		40	56	nC
Q_{gs}	Gate to Source Charge			7		nC
Q_{gd}	Gate to Drain "Miller" Charge			6		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 1.8\text{A}$ (Note 2)		0.7	1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 25\text{A}, di/dt = 100\text{A}/\mu\text{s}$		46	69	ns
Q_{rr}	Reverse Recovery Charge			28	42	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta Jc}$ is determined by the user's board design.



a. 50°C/W when mounted on a 1 in² pad of 2 oz copper.



b. 100°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

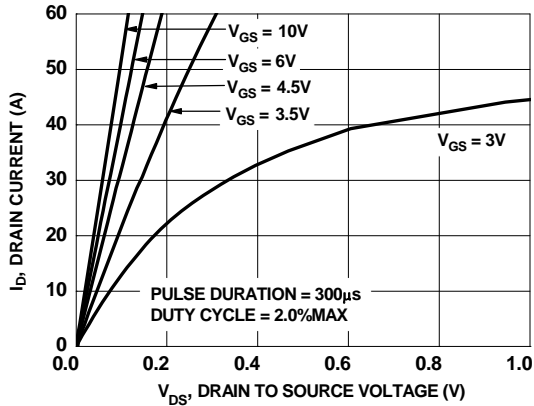


Figure 1. On-Region Characteristics

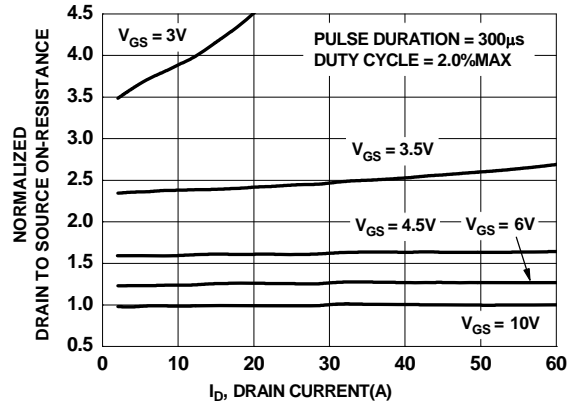


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

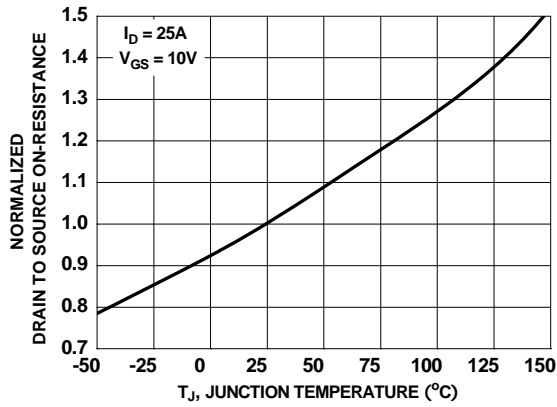


Figure 3. Normalized On-Resistance vs Junction Temperature

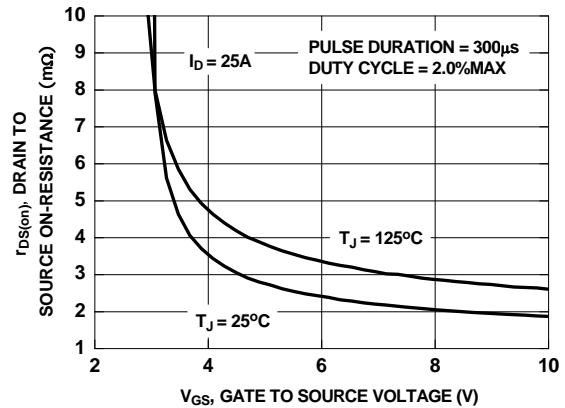


Figure 4. On-Resistance vs Gate to Source Voltage

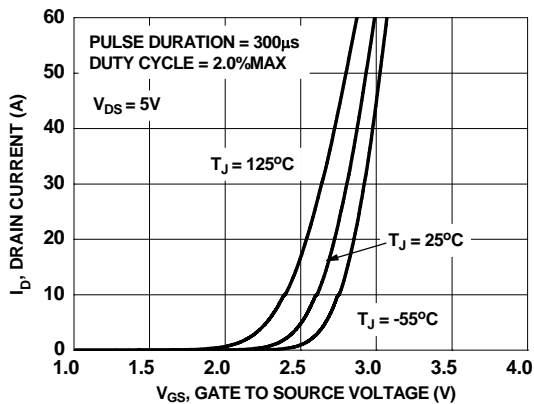


Figure 5. Transfer Characteristics

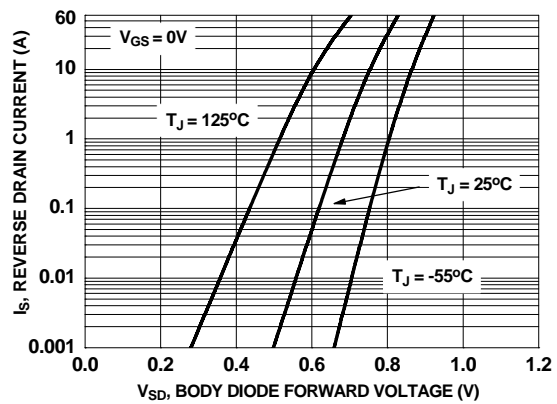


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

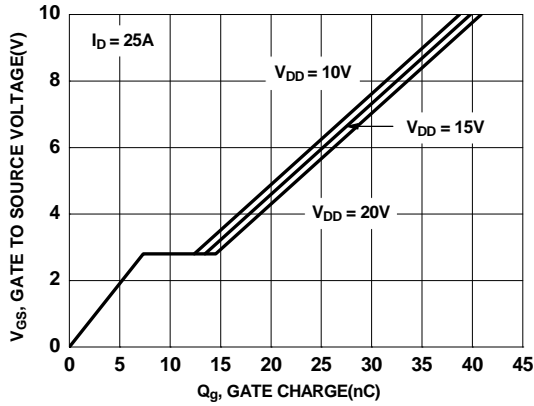


Figure 7. Gate Charge Characteristics

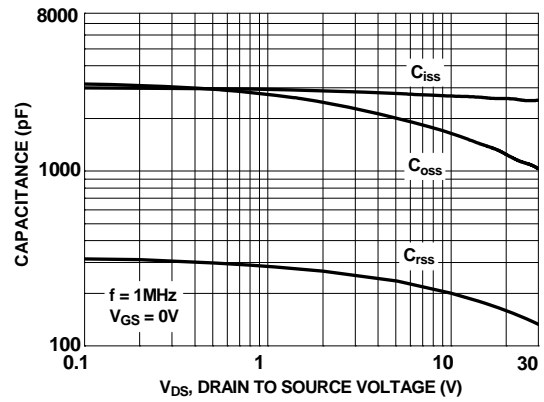


Figure 8. Capacitance vs Drain to Source Voltage

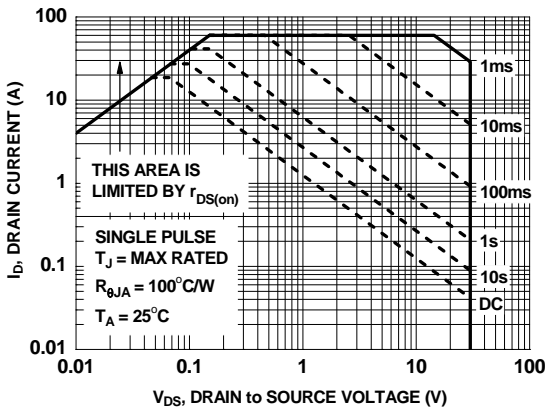


Figure 9. Forward Bias Safe Operating Area

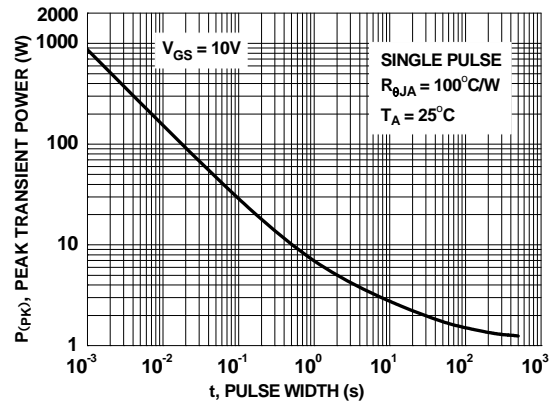


Figure 10. Single Pulse Maximum Power Dissipation

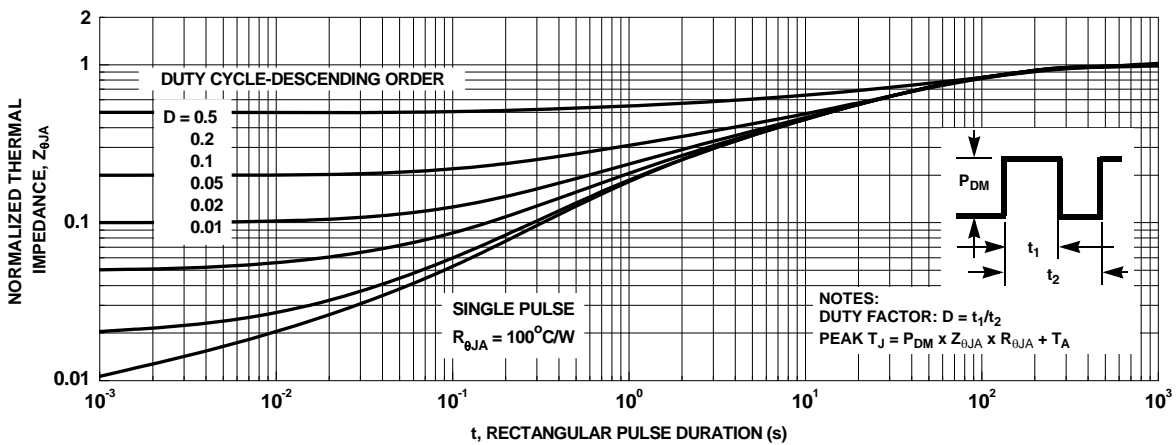
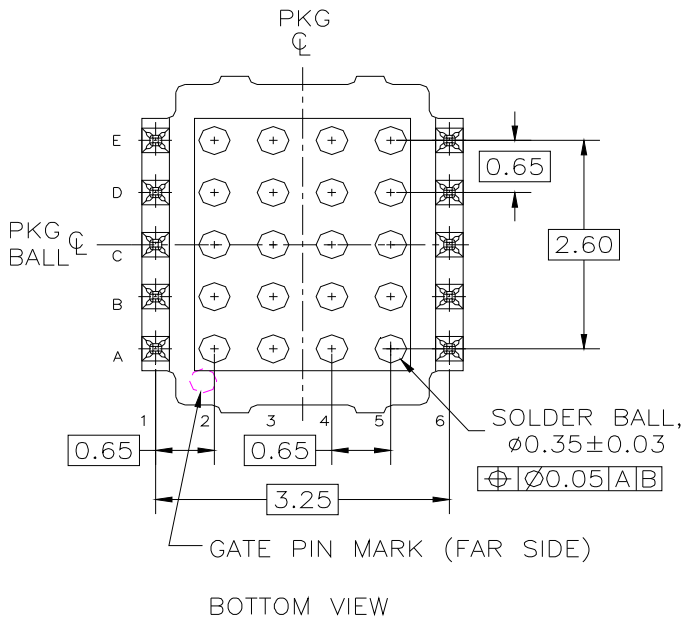
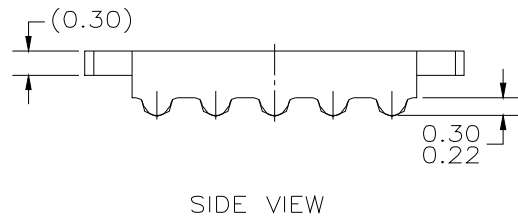
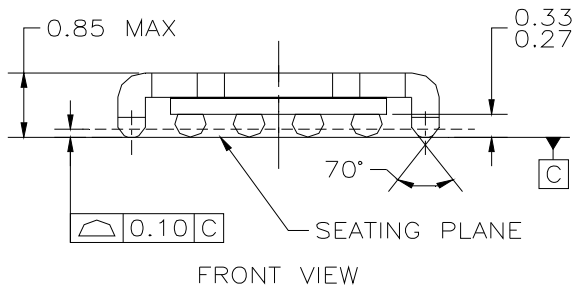
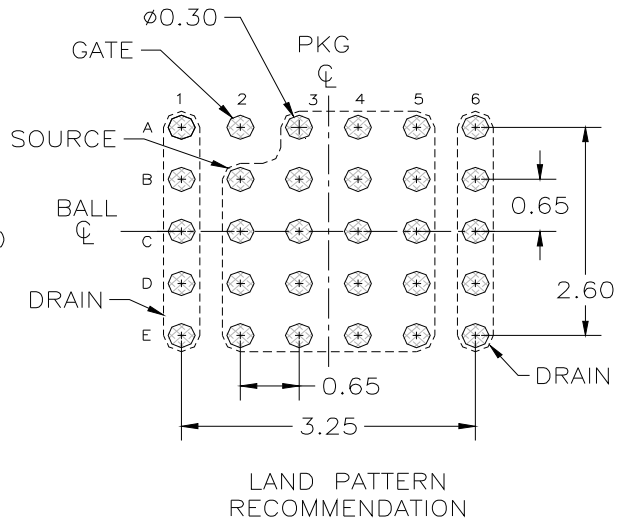
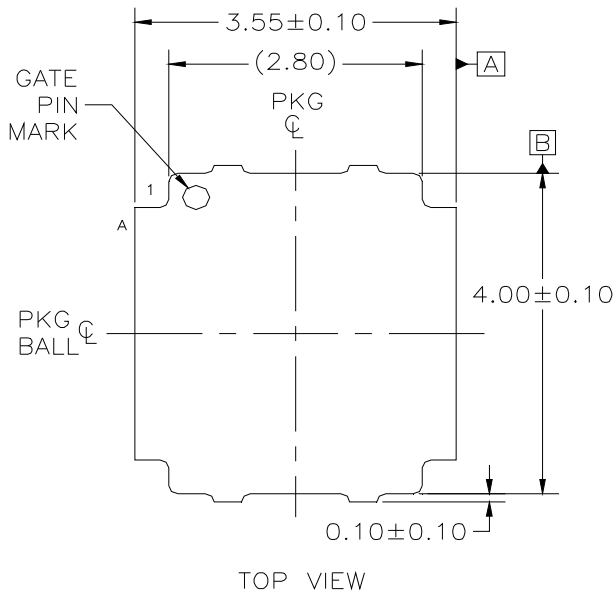


Figure 11. Transient Thermal Response Curve

Dimensional Outline and Pad Layout



- NOTES: UNLESS OTHERWISE SPECIFIED
 A) ALL DIMENSIONS ARE IN MILLIMETERS.
 B) NO JEDEC REGISTRATION REFERENCE AS OF MARCH 2006.
 C) TERMINAL CONFIGURATION TABLE


POSITION	DESIGNATION	TYPE
A1,B1,C1,D1,E1, A6,B6,C6,D6,E6	DRAIN	COPPER STUD
A2	GATE	SOLDER BALL
A3,A4,A5,B2,B3, B4,B5,C2,C3,C4, C5,D2,D3,D4,D5, E2,E3,E4,E5	SOURCE	SOLDER BALL

BGA020CREVA



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